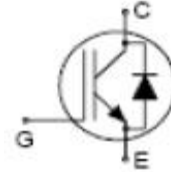


PRELIMINARY DATASHEET

600V 50A, N-Channel IGBT in Trench & Field Stop technology with soft, fast recovery anti-parallel diode, in TO247 Package

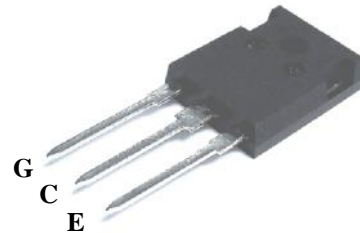
APPLICATION

- Uninterruptible power supplies (UPS)
- Solar inverters
- Welding inverters
- Motor drives
- Low power lighting: low frequency



FEATURES

- Low $V_{CE(sat)}$
- Low turn-off losses
- Short tail current
- Positive temperature coefficient
- Easy paralleling
- Very soft, fast recovery anti-parallel diode
- Pb-free finished; **RoHS compliant**



MAXIMUM RATINGS, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Units
Collector-emitter voltage	V_{CE}	600	V
DC collector current $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	I_C	100 50	A
Pulsed collector current, t_P limited by T_{jmax}	I_{Cpulse}	150	
Turn off safe operating area $V_{CE} \leq 600\text{V}$, $T_J \leq 150^\circ\text{C}$	-	150	
Diode forward current $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	I_F	100 50	
Gate-emitter voltage	V_{GE}	± 20	V
Short circuit withstand time ¹ $V_{GE} = 15\text{V}$, $V_{CC} \leq 400\text{V}$, $T_J \leq 150^\circ\text{C}$	t_{SC}	5	μs
Power dissipation $T_C = 25^\circ\text{C}$	P_{tot}	333	W
Operating junction and storage temperature	T_j, T_{stg}	-55...+175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Max. Value	Units
Characteristics			
IGBT thermal resistance, junction to case	R_{thJC}	0.45	K/W
Diode thermal resistance, junction to case	R_{thJCD}	0.8	

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

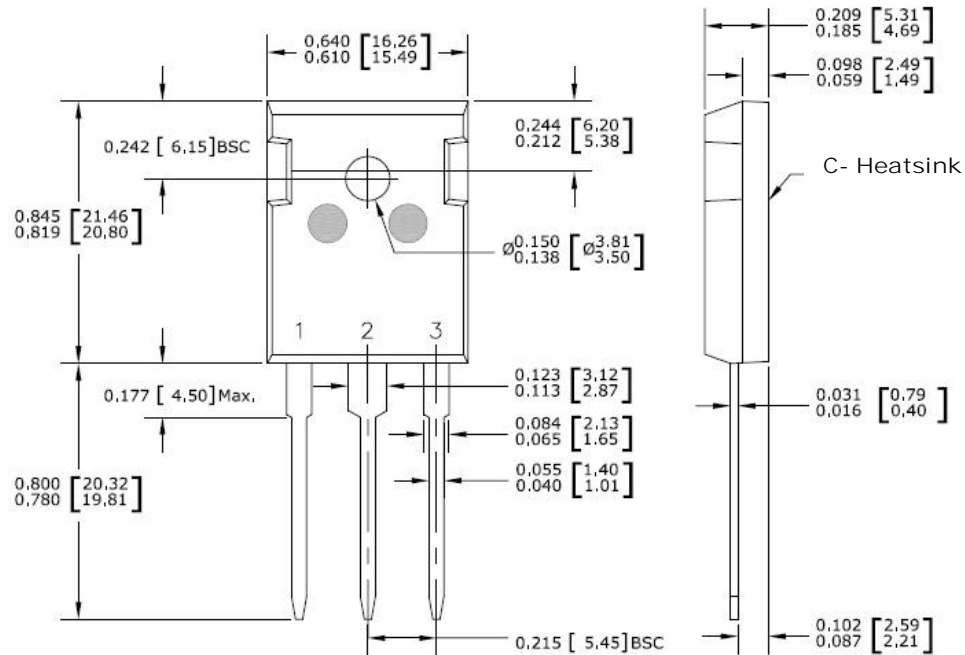
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Characteristics						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0V, I_C = 0.2mA$	600	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C = 50A$	-	1.5	2.0	
Diode forward voltage	V_F	$V_{GE} = 0V, I_F = 50A$	-	1.55	1.95	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C = 0.8mA, V_{CE} = V_{GE}$	4.1	4.9	5.7	
Zero gate voltage collector current	I_{CES}	$V_{CE} = 600V, V_{GE} = 0$	-	-	40	μA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0V, V_{GE} = 20V$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE} = 20V, I_C = 50A$	-	31	-	S
Dynamic Characteristics						
Input capacitance	C_{iss}	$V_{CE} = 25V,$ $V_{GE} = 0V,$ $f = 1MHz$	-	3140	-	pF
Output capacitance	C_{oss}		-	200	-	
Reverse transfer capacitance	C_{riss}		-	93	-	
Gate charge	Q_{Gate}	$V_{CC} = 480V, I_C = 50A$ $V_{GE} = 15V$	-	310	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	13	-	nH
Short circuit collector current ¹	$I_{C(SC)}$	$V_{GE} = 15V, t_{sc} \leq 5\mu s$ $V_{CC} \leq 400V, T_J = 150^\circ C$	-	458	-	A

SWITCHING CHARACTERISTICS, Inductive Load at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
IGBT Characteristics						
Turn-on delay time	$t_{d(on)}$	$T_j = 25^\circ C,$ $V_{CC} = 400V, I_C = 50A,$ $V_{GE} = 0/15V,$ $R_G = 7\Omega,$ Energy losses included tail and diode reverse recovery.	-	26	-	ns
Rise time	t_r		-	29	-	
Turn-off delay time	$t_{d(off)}$		-	299	-	
Fall time	t_f		-	29	-	
Turn-on energy	E_{on}		-	1.2	-	mJ
Turn-off energy	E_{off}		-	1.4	-	
Total switching energy	E_{ts}	-	2.6	-		
Anti-Parallel Diode Characteristics						
Peak Reverse recovery current	I_{rrm}	$I_F = 50A$ $di_F/dt = 2800A/\mu s$ $V_R = 300V$	-	78	-	A
Reverse recovery charge	Q_{rr}	$V_{GE} = 0V$	-	2.25	-	μC

1. Allowed number of short circuits: < 1000; time between short circuits: > 1s.
2. Leakage inductance L_σ and Stray capacity C_σ due to dynamic test circuit.

Package Outline Drawing



CAUTION: These devices are ESD sensitive. Use proper handling procedure.

Disclaimer

These specifications may not be considered as a guarantee of components characteristics. Components have to be tested depending on intended application as adjustments may be necessary. The use of **iQXPRZ Power Inc.** components in life support appliances and systems are subject to written approval of **iQXPRZ Power Inc.**